

Hung Yip Ng
FIS920000192US10JJC

100

Fig. 1A

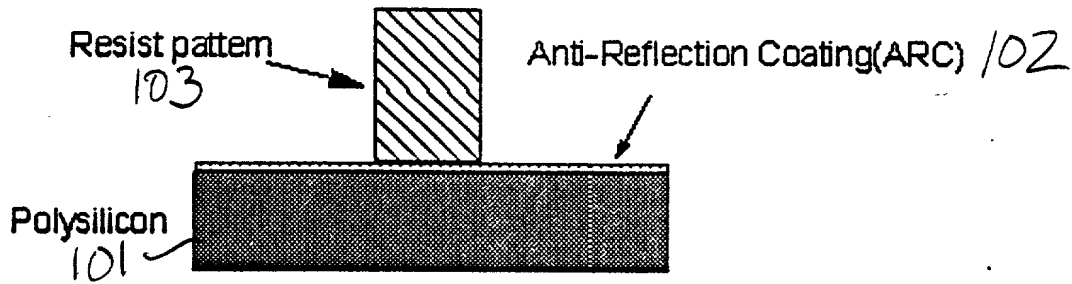


Fig. 1B

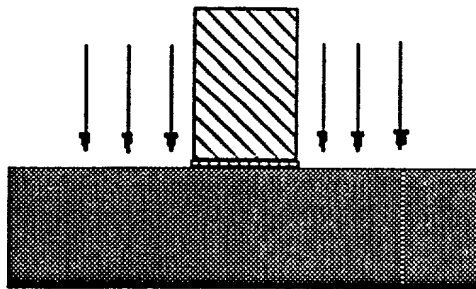
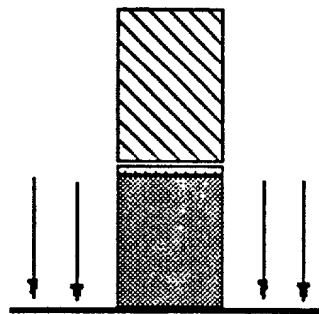
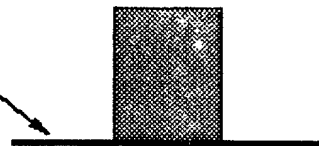


Fig. 1C



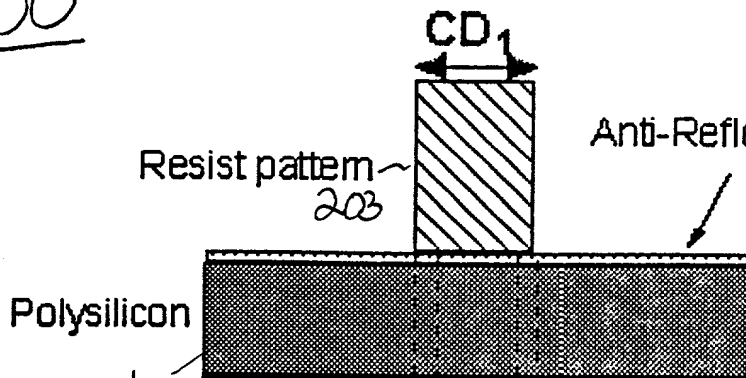
gate oxide 104

Fig. 1D



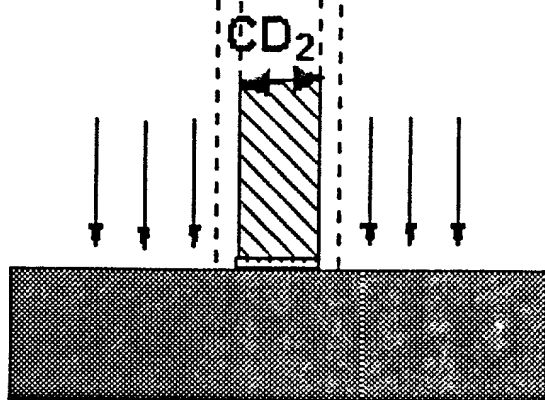
200

Fig. 2A



(1) Litho pattern

Fig. 2B

(2) O₂ etch => trimming! $CD_2 < CD_1$

	Litho tool	Line-width resist	O ₂ trim time	Line-width after trim	Line-width poly	Leff
6X	MSII	0.20	20s	0.18	0.18	0.15
8S	MSIII	0.15	20s	0.13	0.13	0.09
8S2					0.10	0.07

Fig. 2C

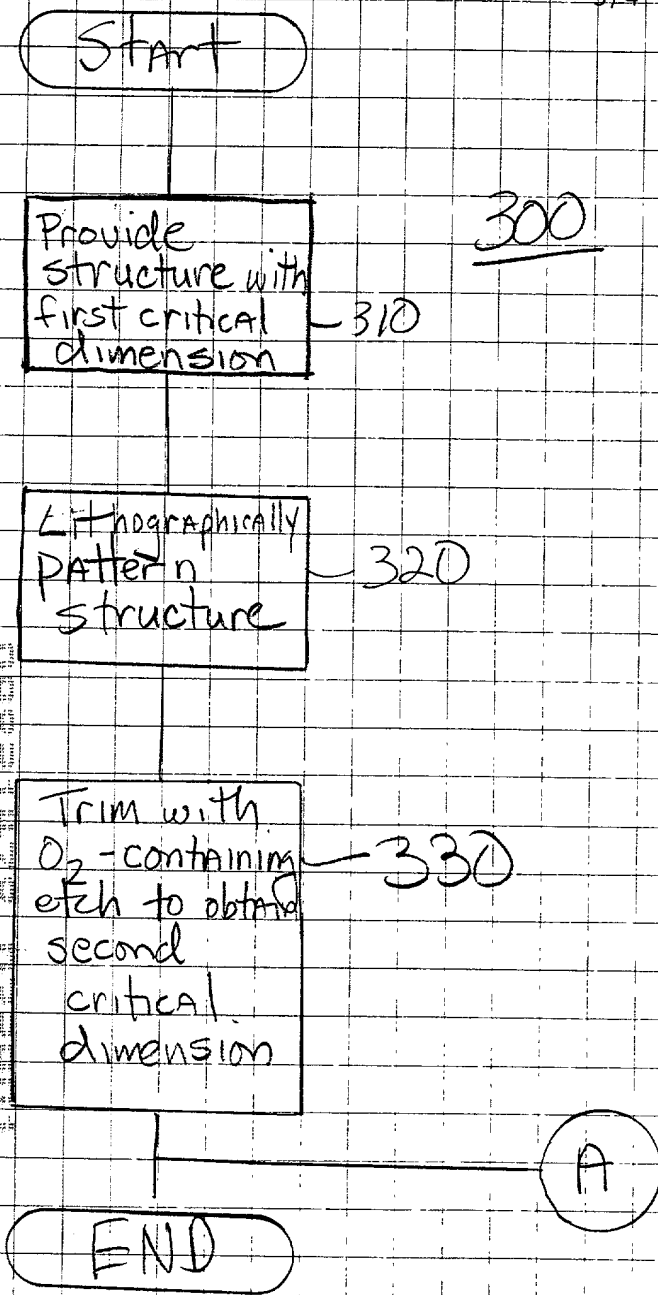


Figure 3

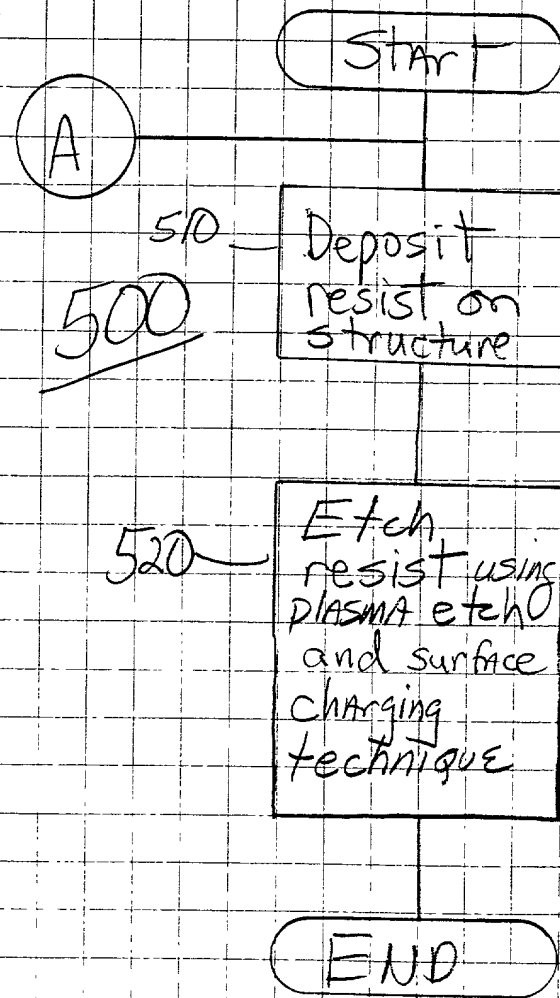


Figure 5

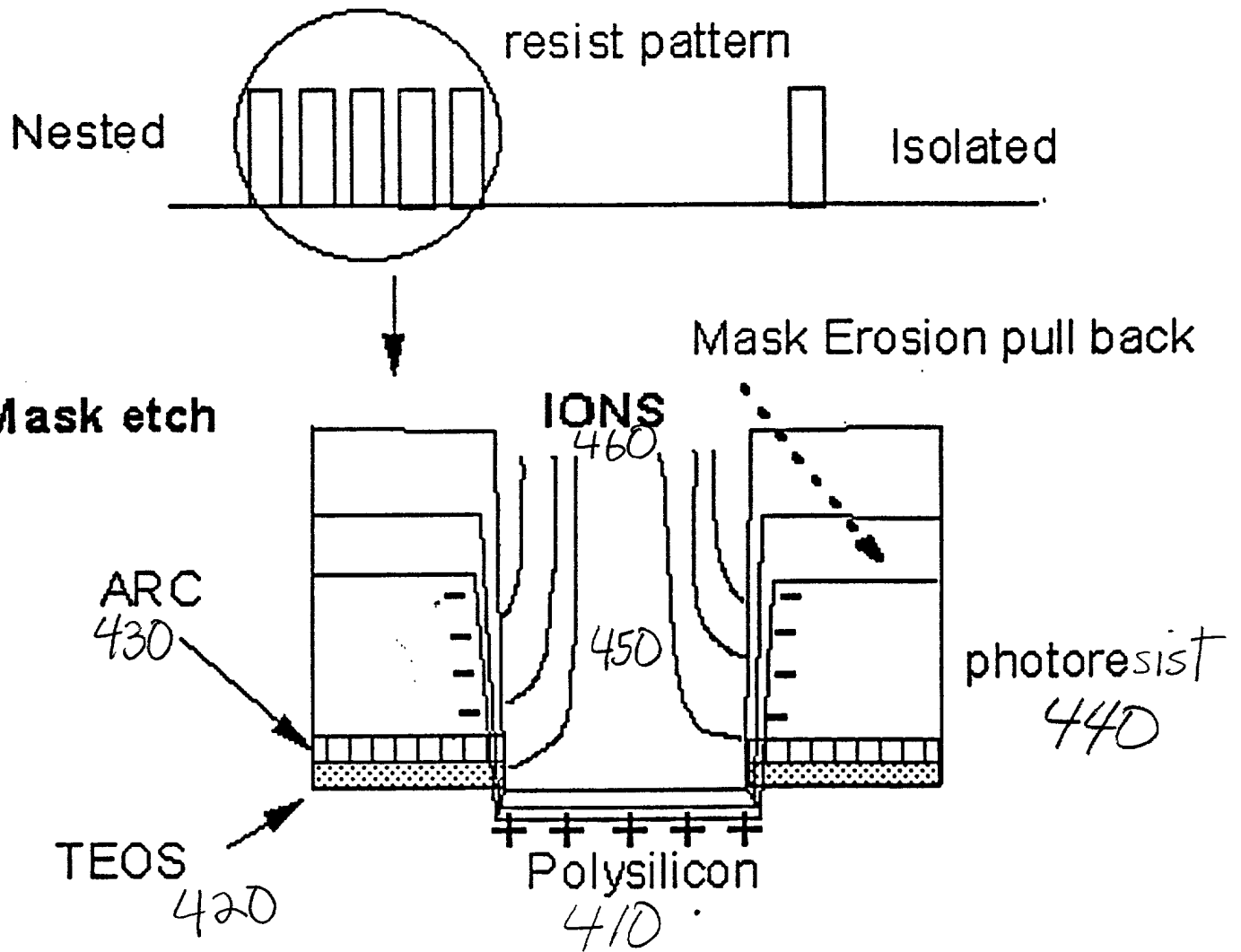
400

Figure 4